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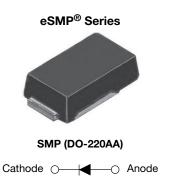
Vishay Semiconductors

COMPLIANT

HALOGEN

FREE

# Ultrafast Rectifier, 2 A FRED Pt®



### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 A				
V <sub>R</sub>	100 V, 200 V				
V <sub>F</sub> at I <sub>F</sub>	0.79 V				
I <sub>FSM</sub>	40 A				
t <sub>rr</sub> (typ.)	23 ns				
T <sub>J</sub> max.	175 °C				
Package	SMP (DO-220AA)				
Circuit configuration	Single				

#### **FEATURES**

- Very low profile typical height of 1.0 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### **TYPICAL APPLICATION**

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

#### **MECHANICAL DATA**

Case: SMP (DO-220AA)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse	VS-2ENH01-M3	W		100	V	
voltage	VS-2ENH02-M3	$V_{RRM}$		200	V	
Average rectified forward current		I <sub>F(AV)</sub>	T <sub>C</sub> = 158 °C	2	^	
Non-repetitive peak surge current		I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 10 ms sine pulse	40	A	
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage,	VS-2ENH01-M3	V <sub>BR</sub> ,	L = 100 · A	100	-	-	
blocking voltage	VS-2ENH02-M3	$V_R$		200	-	-	V
Forward voltage V <sub>F</sub>		V	I <sub>F</sub> = 2 A	-	0.94	1.00	]
		I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C	-	0.79	0.84		
Reverse leakage current		ı	$V_R = V_R$ rated	-	-	2	μА
		I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	-	20	
Junction capacitance		C <sub>T</sub>	V <sub>R</sub> = 200 V	-	8	-	pF



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	23	-	
Reverse recovery time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	28	
		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 2 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 100 V	-	16	-	ns A
		T <sub>J</sub> = 125 °C		-	25	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.0	=	
		T <sub>J</sub> = 125 °C		-	3.1	-	
Reverse recovery charge Q <sub>rr</sub>	0	T <sub>J</sub> = 25 °C		-	15	-	
	T <sub>J</sub> = 125 °C		-	37	=	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER SYMBOL TEST CONDITION		TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction temperature ran	•	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistar junction to mour	*	R <sub>thJM</sub> <sup>(1)</sup>	Infinite heatsink	-	7	9	°C/W
Thermal resistar junction to ambi	*	R <sub>thJA</sub>	PCB footprint 4.8 mm x 4.8 mm	-	107	-	- C/VV
Marking device	VS-2ENH01-M3		2H1			<del>-</del> 11	
iviai kii ig device	VS-2ENH02-M3		Case style SMP (DO-220AA)	2H2			

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

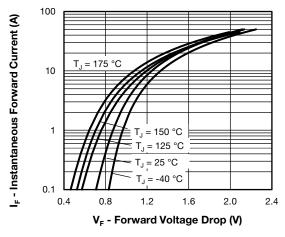


Fig. 1 - Typical Forward Voltage Drop Characteristics

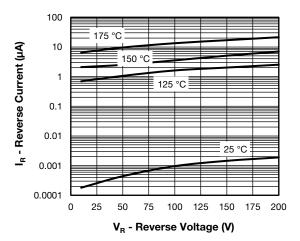


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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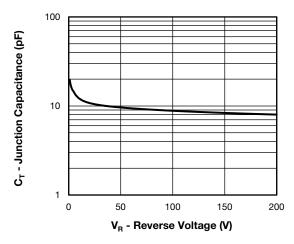


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

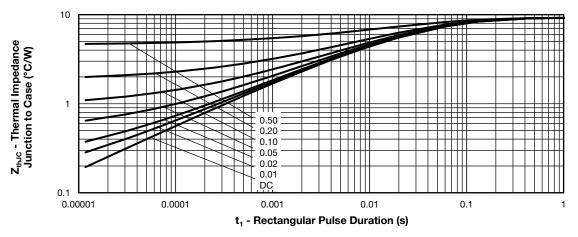


Fig. 4 - Transient Thermal Impedance, Junction to Case

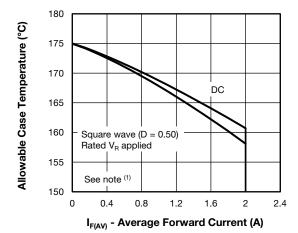


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

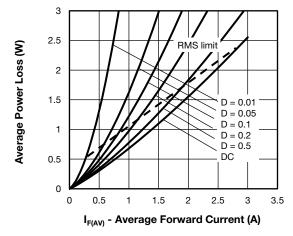


Fig. 6 - Forward Power Loss Characteristics

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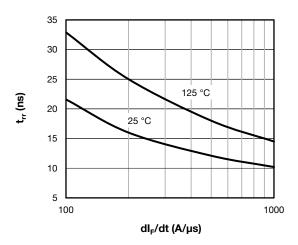


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

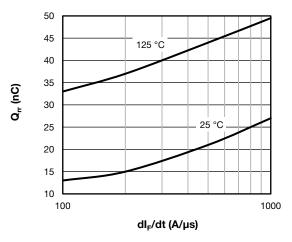
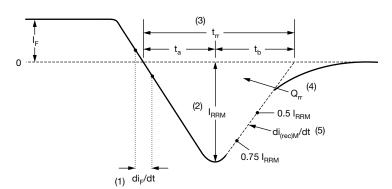


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75  $I_{RRM}$  and 0.50  $I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

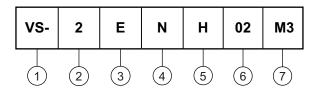
Fig. 9 - Reverse Recovery Waveform and Definitions

# VS-2ENH01-M3, VS-2ENH02-M3

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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (2 = 2 A)

Circuit configuration:

E = single diode

N = SMP package

5 - Process type,

H = ultrafast recovery

6 - Voltage code (02 = 200 V)

7 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	PREFERRED PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-2ENH01-M3/84A	84A	3000	7" diameter plastic tape and reel			
VS-2ENH01-M3/85A	85A	10 000	13" diameter plastic tape and reel			
VS-2ENH02-M3/84A	84A	3000	7" diameter plastic tape and reel			
VS-2ENH02-M3/85A	85A	10 000	13" diameter plastic tape and reel			

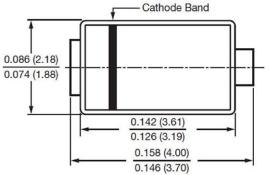
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96547</u>				
Part marking information	www.vishay.com/doc?96574			
Packaging information	www.vishay.com/doc?88869			
SPICE model	www.vishay.com/doc?96551			

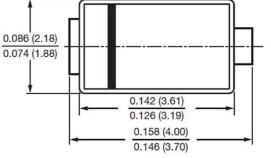


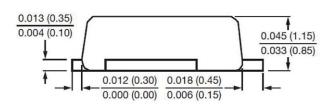
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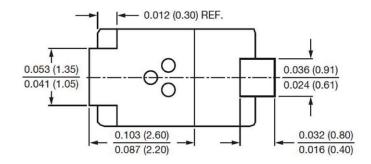
# **SMP (DO-220AA)**

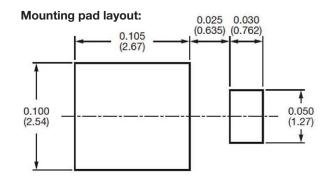
### **DIMENSIONS** in inches (millimeters)













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